

Title (en)

Method and apparatus for heat-treating an SOI substrate and method of preparing an SOI substrate by using the same

Title (de)

Verfahren und Gerät zur Wärmebehandlung eines SOI Substrats und damit durchgeführte Präparationsmethode eines SOI Substrats

Title (fr)

Procédé et appareil pour un traitement thermique d'un substrat SOI et procédé de préparation d'un substrat SOI

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Application

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Priority

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Abstract (en)

With a method according to the invention, an SOI substrate having on the surface thereof a single crystal silicon film formed on an insulator is heat-treated in a hydrogen-containing reducing atmosphere in order to smooth the surface and reduce the boron concentration without damaging the film thickness uniformity in a single wafer and among different wafers. The method is characterized in that the single crystal silicon film is arranged opposite to a member of non-oxidized silicon for heat treatment. <IMAGE>

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IPC 8 full level

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Citation (applicant)

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